

FIG. 1A

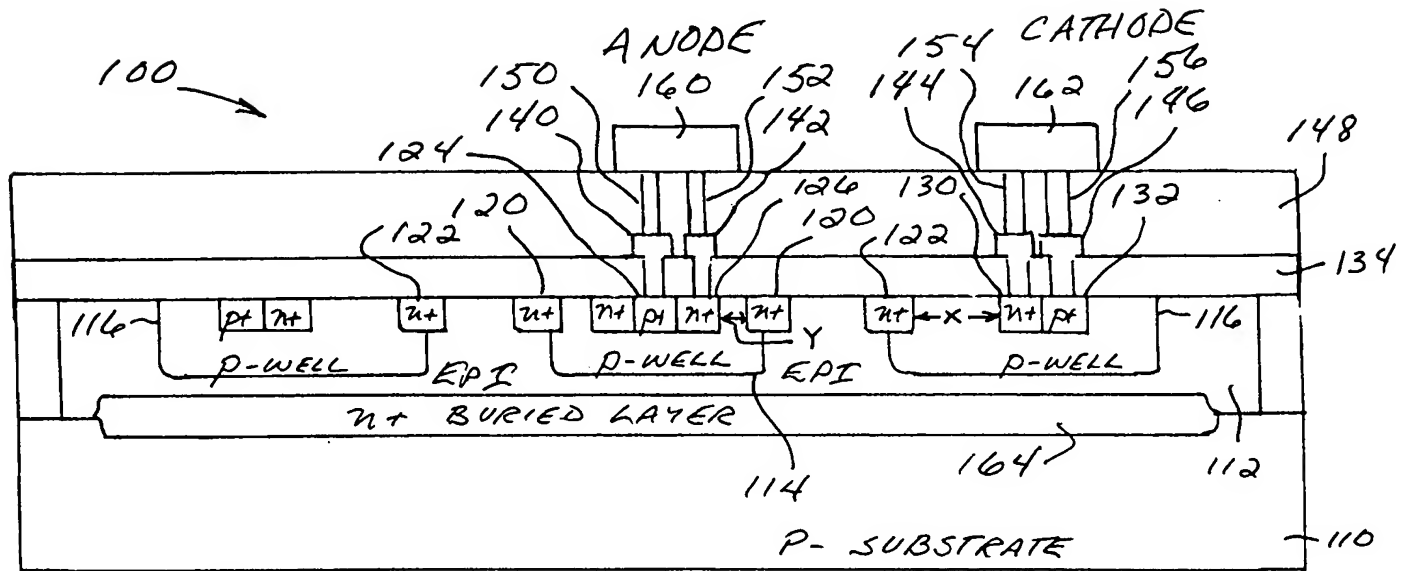


FIG. 1B

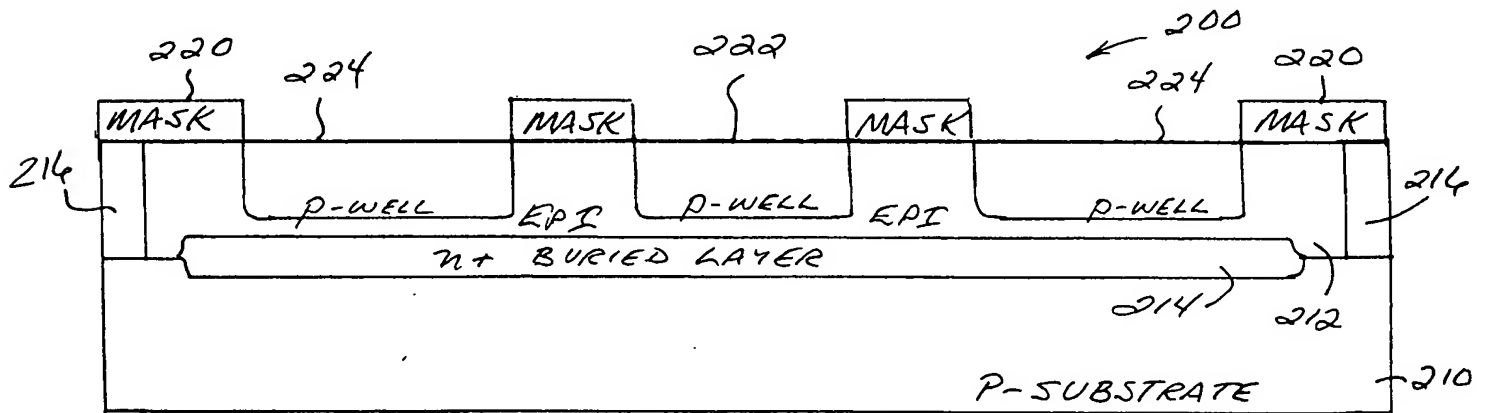


FIG. 2A

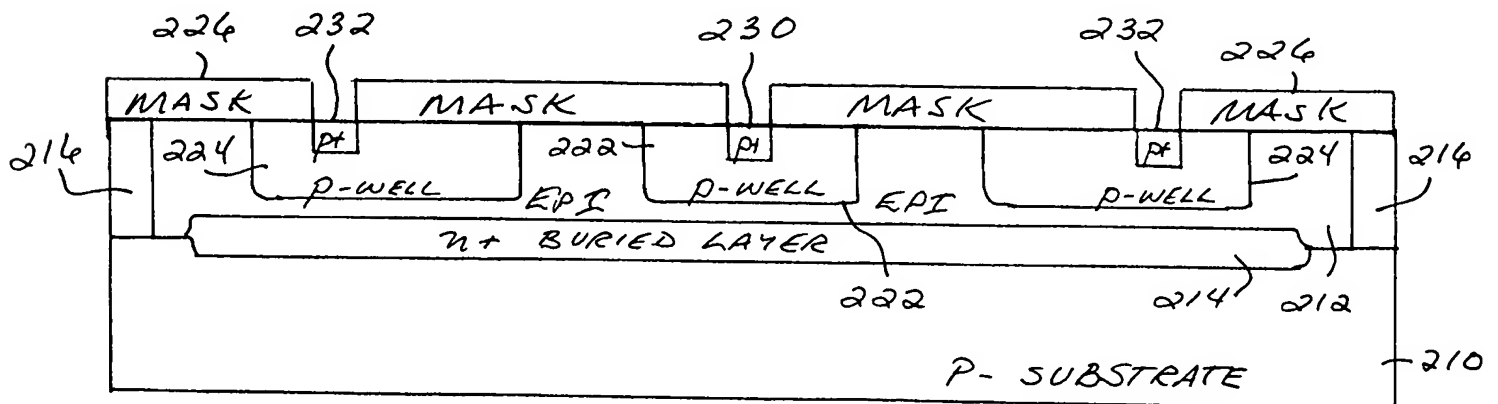


FIG. 2B

[illegible]

A cross-sectional view of a semiconductor device. The top layer is labeled METAL. Below it are regions labeled P-WELL, EPI, and P-WELL. A central n+ BURIED LAYER is shown. The bottom layer is labeled P-SUBSTRATE. Various components are numbered: 272, 260, 262, 264, 266, 270, 268, 250, 216, 232, 246, 242, 240, 244, 224, 222, 214, 212, 210.

FIG. 2E

